

ABSTRACT

In an inventive circuit simulation method, simulation is performed utilizing a circuit simulator, based on a netlist prepared using mask layout data for a circuit, and parameters obtained from measurement data concerning the characteristic of each transistor. The parameters are extracted from the measurement data based on not only the transistor size but also a stress applied to the transistor. Therefore, the circuit simulation can be performed with precision and accuracy never before possible, in consideration of a change in the characteristic of the transistor which is caused by the stress applied thereto.